Product data sheet

1. General description

Planar passivated SCR with sensitive gate in a SOT428 (DPAK) surface mountable plastic package. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Sensitive gate
- Planar passivated for voltage ruggedness and reliability
- Direct triggering from low power drivers and logic ICs
- Surface mountable package

3. Applications

- General purpose switching
- Protection Circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		[1]	-	-	600	V
V_{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$; Fig. 4; Fig. 5		-	-	35	А
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 111 ^{\circ}\text{C}$; Fig. 2; Fig. 3		-	-	4	Α
Static characteristics							
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$		-	15	200	μΑ

^[1] Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	A - [] - K
2	Α	anode[1]		Ğ sym037
3	G	gate		ŕ
mb	А	mounting base; connected to anode	1 3	
			DPAK (SOT428)	

^[1] It is not possible to connect to pin 2 of the SOT428 package.

6. Ordering information

Table 3. Ordering information

Type number		Package		
		Name	Description	Version
	BT150S-600R	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		[1]	-	600	V
V_{RRM}	repetitive peak reverse voltage			-	600	V
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 111 °C; <u>Fig. 1</u>		-	2.5	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 111 ^{\circ}\text{C}$; Fig. 2; Fig. 3		-	4	А
I _{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$; Fig. 4; Fig. 5		-	35	А
		half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 8.3 \text{ms}$		-	38	А
l ² t	I ² t for fusing	t _p = 10 ms; SIN		-	6.1	A ² s
dI _T /dt	rate of rise of on-state current	$I_T = 10 \text{ A}$; $I_G = 50 \text{ mA}$; $dI_G/dt = 50 \text{ mA}/$ µs		-	50	A/µs
I _{GM}	peak gate current			-	2	Α
V_{RGM}	peak reverse gate voltage			-	5	V
P _{GM}	peak gate power			-	5	W
P _{G(AV)}	average gate power	over any 20 ms period		-	0.5	W
T _{stg}	storage temperature			-40	150	°C
T _j	junction temperature		<u>[2]</u>	-	125	°C

^[1] Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.

^[2] Operation above 110°C may require the use of a gate to cathode resistor of $1k\Omega$ or less.

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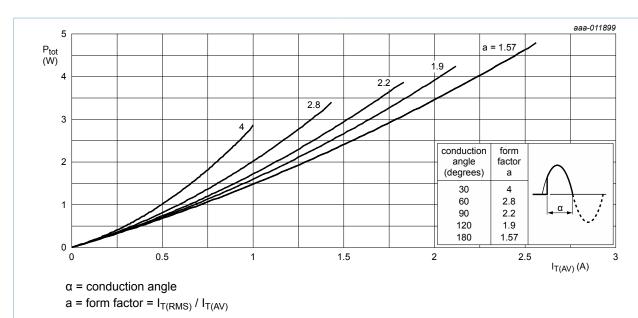


Fig. 1. Total power dissipation as a function of average on-state current; maximum values

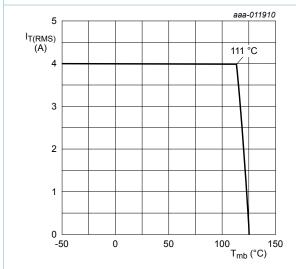
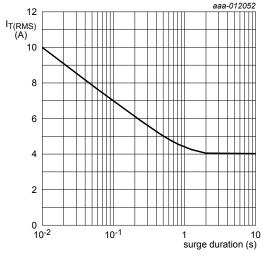


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{mb} = 111 ^{\circ}\text{C}$

Fig. 3. RMS on-state current as a function of surge duration; maximum values

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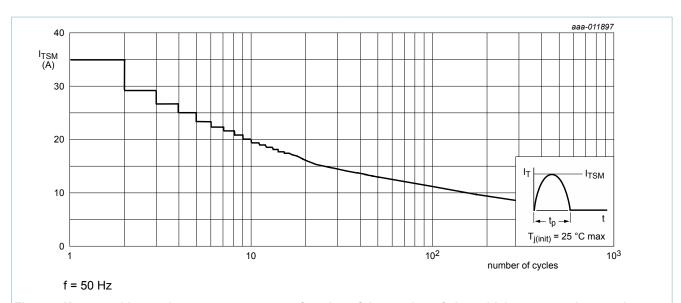


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

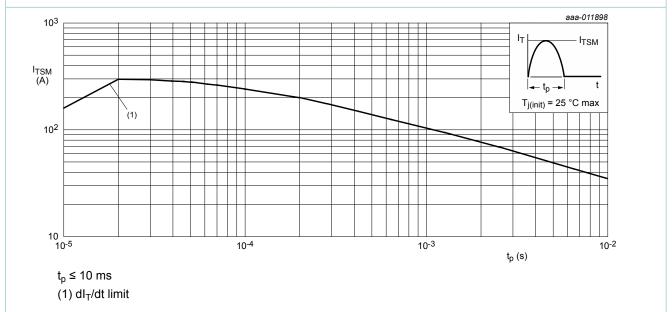


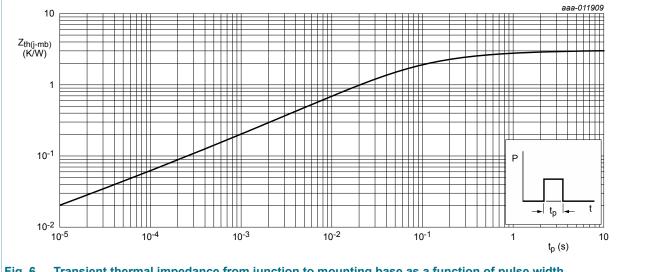
Fig. 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

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Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 6	-	-	3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Device mounted on an FR4 Printed- Circuit Board (PCB), single-sided copper, tin-plated and standard footprint	-	75	-	K/W



Transient thermal impedance from junction to mounting base as a function of pulse width

SCR

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 7</u>	-	15	200	μA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 8$	-	0.17	10	mA
l _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	0.1	6	mA
V_{T}	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.23	1.8	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11	-	0.4	1	V
		$V_D = 600 \text{ V}; I_T = 0.1 \text{ A}; T_j = 110 \text{ °C};$ Fig. 11	0.1	0.2	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
I _R	reverse current	V _R = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic c	haracteristics		'			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; R_{GK} = 100 Ω; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; Fig. 12	-	50	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 10 A; V_D = 600 V; I_G = 5 mA; $dI_G/$ dt = 0.2 A/µs; T_j = 25 °C	-	2	-	μs
t _q	commutated turn-off time	V_{DM} = 402 V; T_j = 125 °C; I_{TM} = 8 A; V_R = 10 V; $(dI_T/dt)_M$ = 10 A/ μ s; dV_D/dt = 2 V/ μ s; R_{GK} = 1 k Ω ; $(V_{DM}$ = 67% of $V_{DRM})$	-	100	-	μs

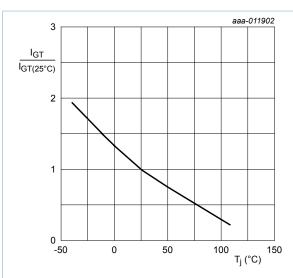


Fig. 7. Normalized gate trigger current as a function of junction temperature

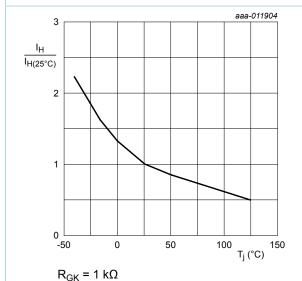
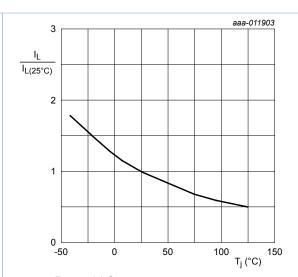
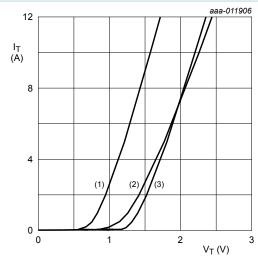


Fig. 9. Normalized holding current as a function of junction temperature



 $R_{GK} = 1 k\Omega$

Fig. 8. Normalized latching current as a function of junction temperature



 $V_0 = 1.26 \text{ V}; R_s = 0.099 \Omega$

(1) T_i = 125 °C; typical values

(2) T_i = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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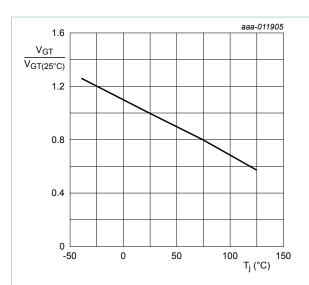


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

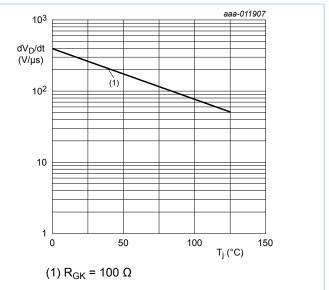


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

10. Package outline

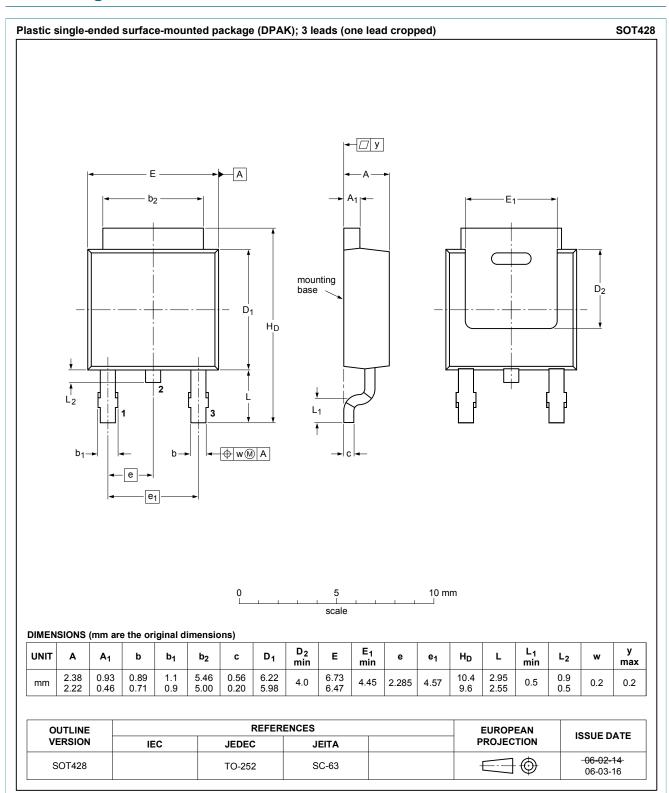
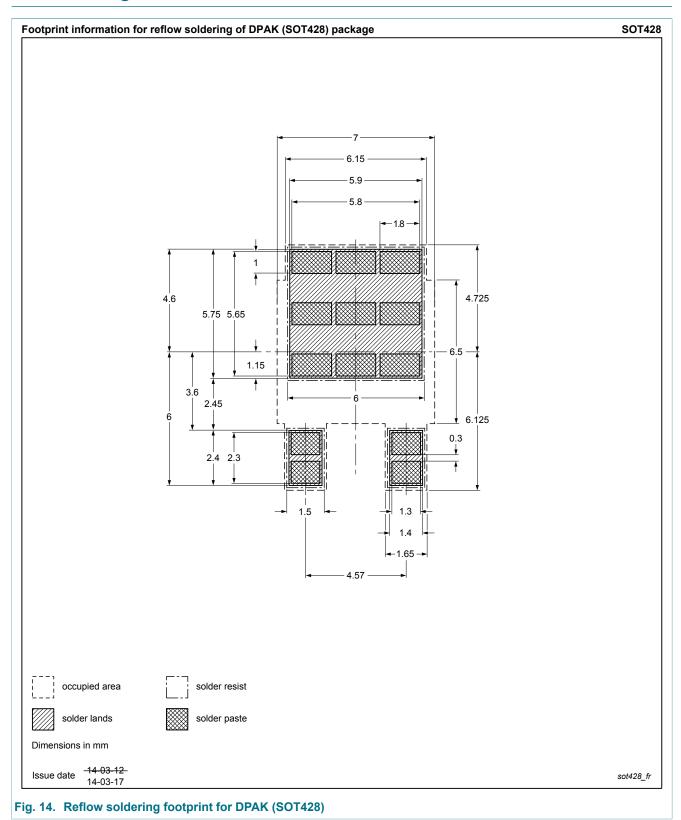


Fig. 13. Package outline DPAK (SOT428)

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11. Soldering



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12. Legal information

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